

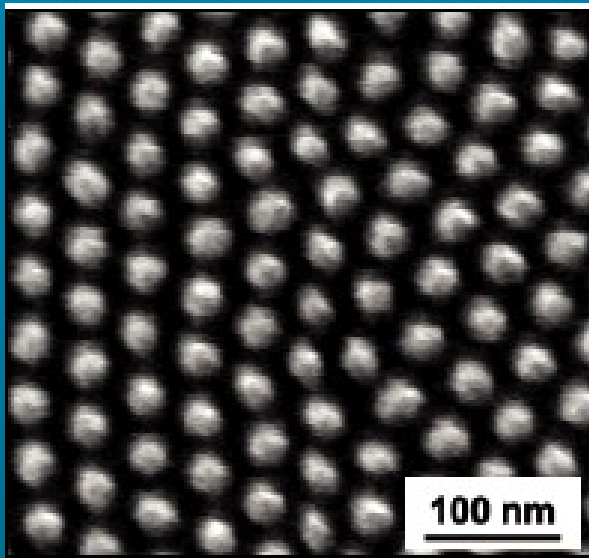
Felületi mintázatképződés rácsgázok segítségével

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Motivation

In nanotechnologies large areas of **nanopatterns** are needed fabricated today by expensive techniques, e.g. electron beam lithography or direct writing with electron and ion beams.



Top Down Process



Start with bulk wafer



Apply layer of photoresist



Expose wafer with UV light through mask and etch wafer



Etched wafer with desired pattern

Bottom Up Process



Start with bulk wafer



Alter area of wafer where structure is to be created by adding polymer or seed crystals or other techniques.



Grow or assemble the structure on the area determined by the seed crystals or polymer. (self assembly)

Similar phenomena: sand dunes, chemical reactions ... → **Universality**
Better understanding of basic surface growth phenomena by STATPHYS

The Kardar-Parisi-Zhang (KPZ) equation/classes

$$\partial_t h(x,t) = \sigma \nabla^2 h(x,t) + \lambda (\nabla h(x,t))^2 + \eta(x,t)$$

σ : (smoothing) surface tension coefficient

λ : local growth velocity, up-down anisotropy

η : roughens the surface by a zero-average, Gaussian noise field with correlator:

$$\langle \eta(x,t) \eta(x',t') \rangle = 2 D \delta^d(x-x')(t-t')$$

Up-down symmetrical case: $\lambda = 0$: Edwards-Wilkinson (EW) equation/classes

Characterization of surface growth:

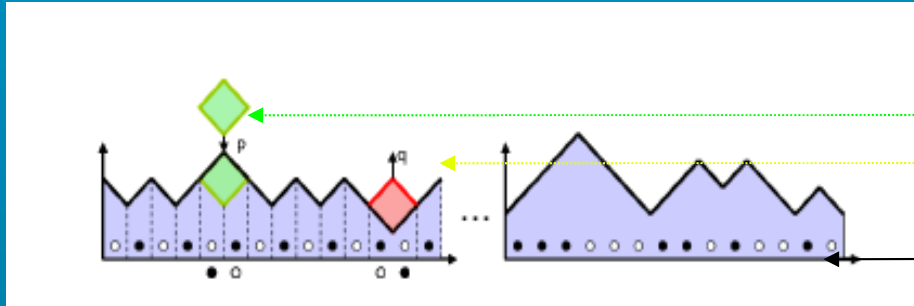
Interface Width:

$$W(L,t) = \left[\frac{1}{L^2} \sum_{i,j} h_{i,j}^2(t) - \left(\frac{1}{L} \sum_{i,j} h_{i,j}(t) \right)^2 \right]^{1/2}$$

Family-Vicsek scaling:

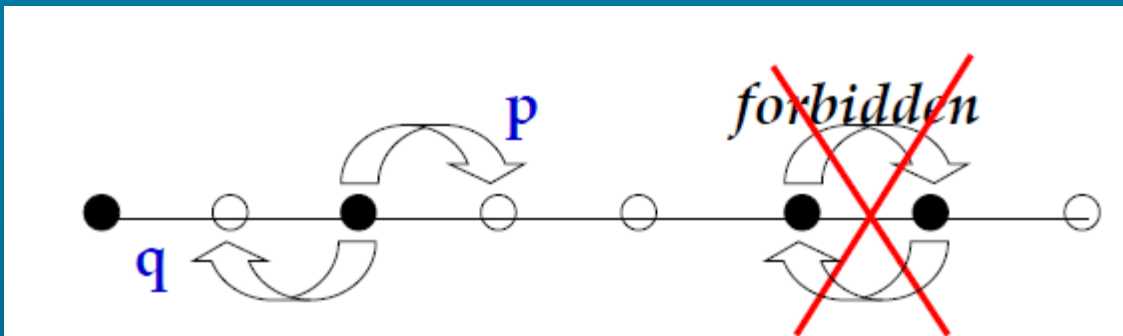
$$\begin{aligned} W(L,t) &\propto t^\beta, \text{ for } t_0 \ll t \ll t_s \\ &\propto L^\alpha, \text{ for } t \gg t_s. \end{aligned}$$

Mappings of KPZ onto lattice gas system in 1d



Kawasaki' exchange of particles

- Mapping of the $1+1$ dimensional surface growth onto the 1d *ASEP* model:
Attachment (with probability p) and **Detachment** (with probability q) corresponds to anisotropic diffusion of particles (bullets) along the $1d$ base space (*M. Plischke, Rácz and Liu, PRB 35, 3485 (1987)*)



The simple *ASEP* (Liggett '95) is **exactly solved 1d lattice gas**

Many features (response to disorder, different boundary conditions ...) are known.

Mappings of KPZ growth in 2+1 dimensions

Octahedron model \sim Generalized ASEP:
Driven diffusive gas of pairs (**dimers**)

G. Ódor, B. Liedke and K.-H. Heinig, PRE79, 021125 (2009) derivation of mapping

Generalized Kawasaki update:

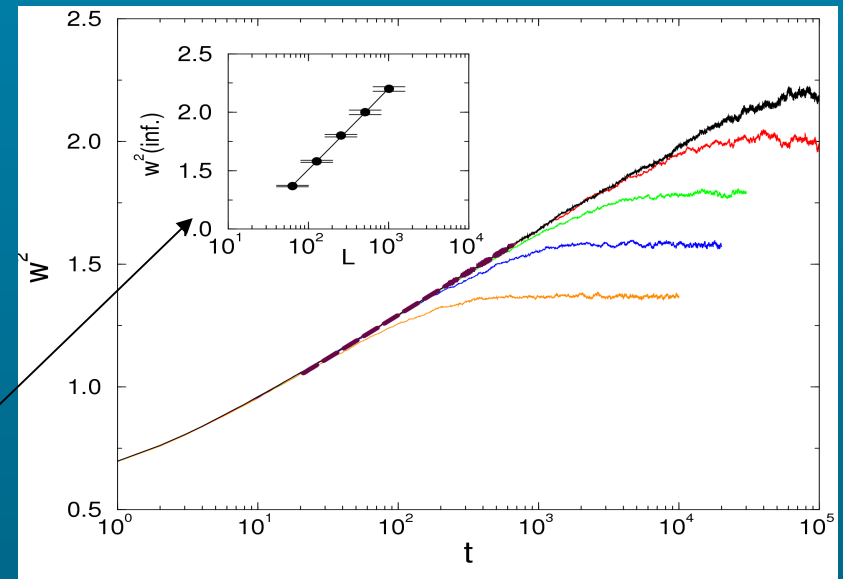
$$\begin{pmatrix} -1 & p \\ -1 & q \end{pmatrix} \Rightarrow \begin{pmatrix} 1 & -1 \\ 1 & -1 \end{pmatrix}$$

- For $p = q = 1$ Edwards-Wilkinson (EW) scaling:

$$W^2(t) = 0.152 \ln(t) + b \quad \text{for } t < t_{sat}$$

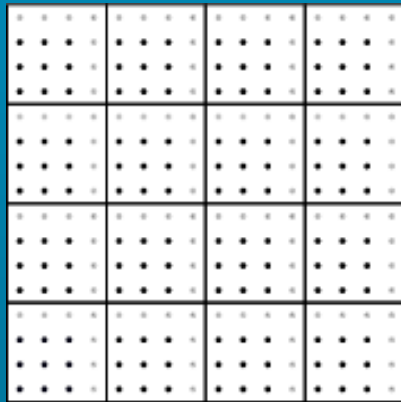
$$W^2(L) = 0.304 \ln(L) + d \quad \text{for } t > t_{sat}$$

2d problem is reduced to quasi 1d
dynamics of reconstructing dimers

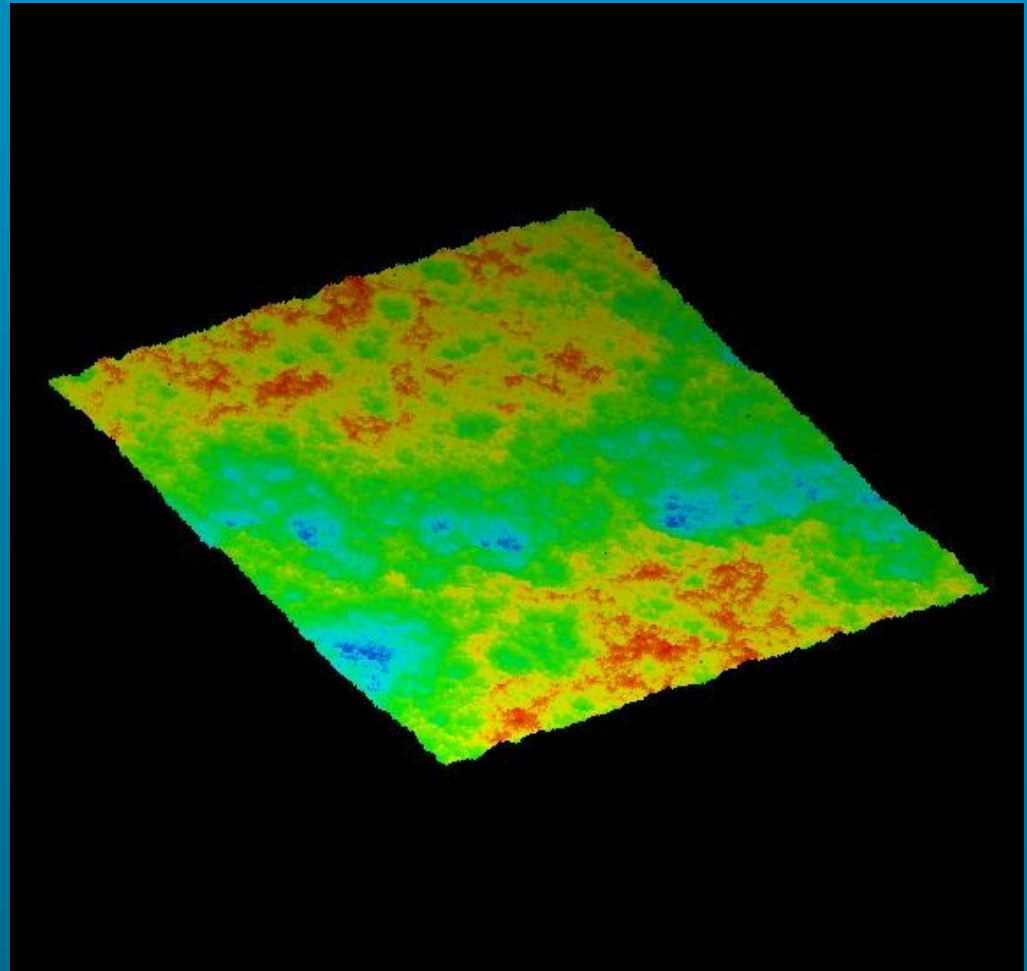


Simulation on graphics card (GPU)

- Checkerboard decomposition
- Sub-systems are loaded in shared memory of GPUs updated with inactive (grey) boundaries:

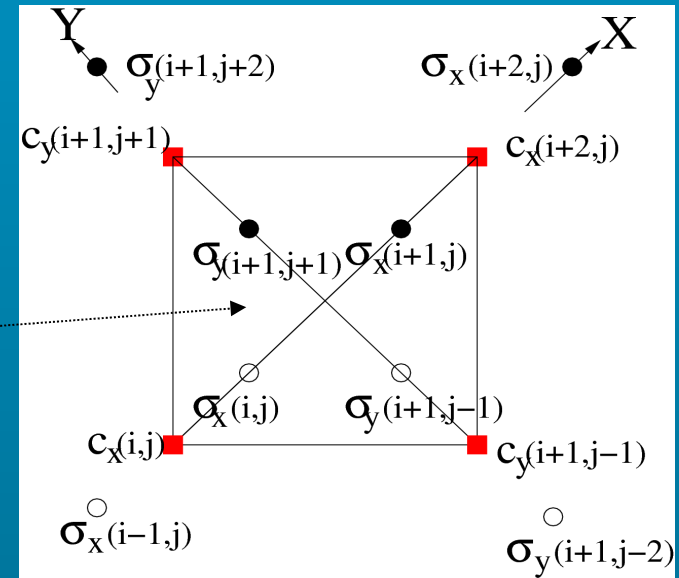
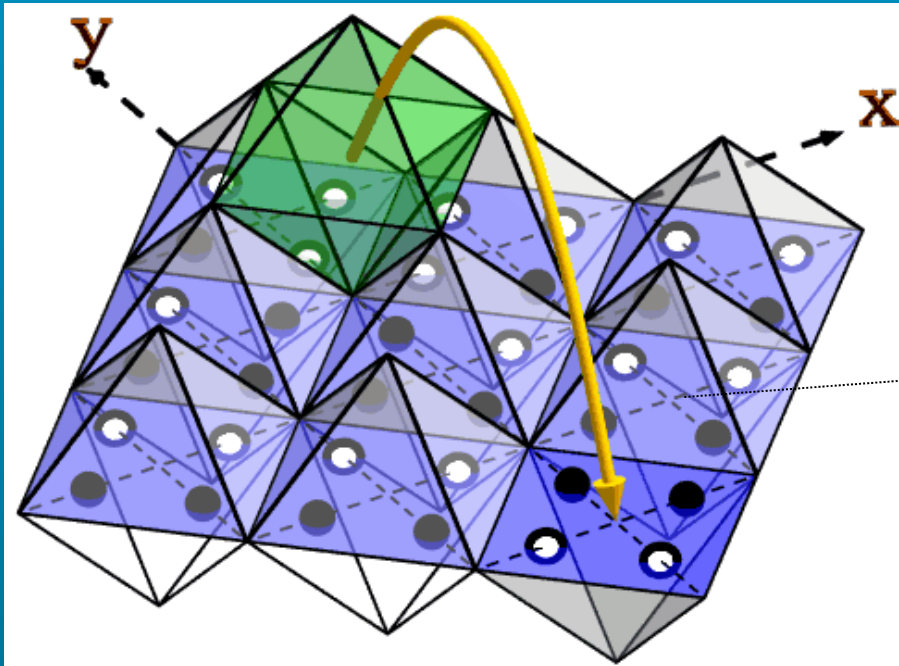


- Each 32-bit word stores the slopes of 4 x 4 sites
- Origin of decomposition moves at every MCs
- **Speedup 240 x to 2.8GHz CPU on 128.000 x 128.000 lattices**



Surface diffusion (Molecular Beam Epitaxy classes)

- Simultaneous octahedron deposition/removal:
Attracting (smoothing diffusion) or *repelling* (roughening diff.) dimers



Two versions based on local configurations

a) Larger height octahedron model
 LHOD

b) Larger curvature octahedron model
 LCOD:



$$c_x(i, j) = \sigma_x(i, j)\sigma_x(i + 1, j)$$

$$\Delta H = \Delta \sum_{\chi=x,y} \sum_{(i,j)} c_\chi(i, j) + \Delta \sum_{\chi=x,y} \sum_{(i',j')} c_\chi(i', j')$$

$$w_{i \rightarrow i'} = 1/2[1 - a \tanh(-\Delta H^2)]$$

Pattern formation by the octahedron model

Competing **KPZ** and **surface diffusion** (following Bradley-Harper theory):

Noisy **Kuramoto-Sivashinsky (KS)** equation (**KPZ** + **Mullins Diffusion**):

$$\partial_t h(x,t) = \sigma \nabla^2 h(x,t) + \lambda (\nabla h(x,t))^2 + \eta(x,t) + \kappa \nabla^4 h(x,t)$$


To generate **patterns inverse** (uphill) diffusion is added !

Inverse KS is studied here, signs of couplings are flipped

Alternating application of deposition/removal (probabilities.: p, q)
and surface diffusion (probabilities: D_x, D_y)

Scaling behavior of 2d **Kuramoto-Sivashinsky** ~ **KPZ** ???
Field Theoretical hypothesis 1995 (*Cuerno et al.*)

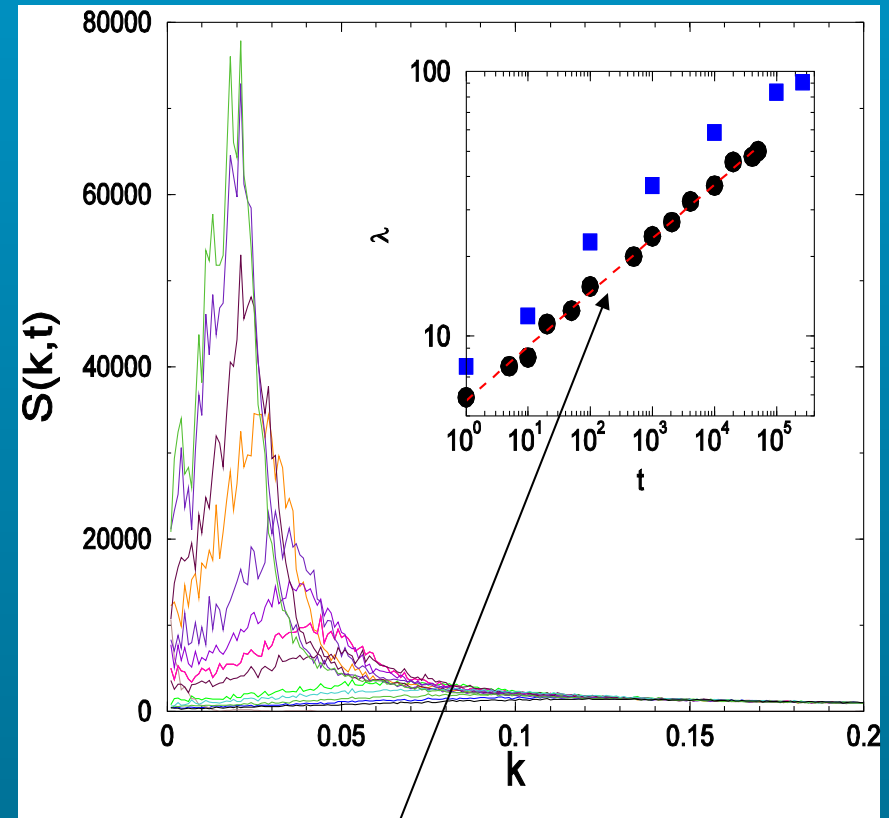
Isotropic surface diffusion

Dimer lattice gas simulation



$$D_x = D_y = 1, \quad p = q = 0.005$$

Power Spectrum Density



The wavelength λ calculated from the PSD:

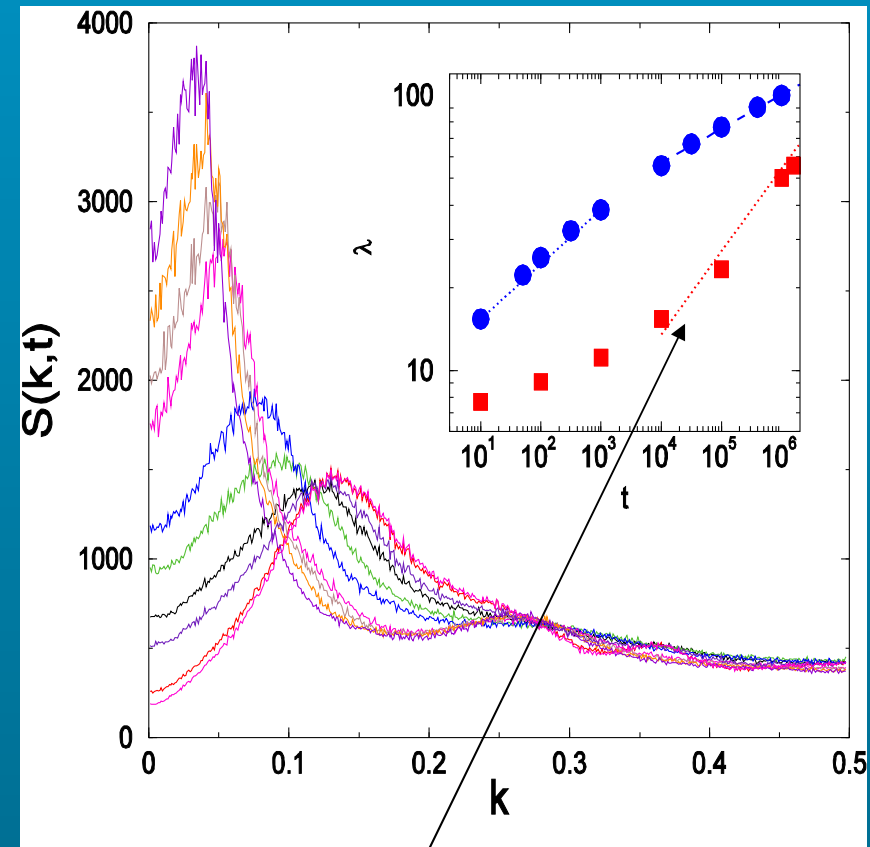
$$\lambda \propto t^{0.2}$$

Both for the LHOD, LCOD cases

Anisotropic surface diffusion:

$$\kappa_x \partial_x^4 h(x,t) + \kappa_y \partial_y^4 h(x,t)$$

Power Spectrum Density

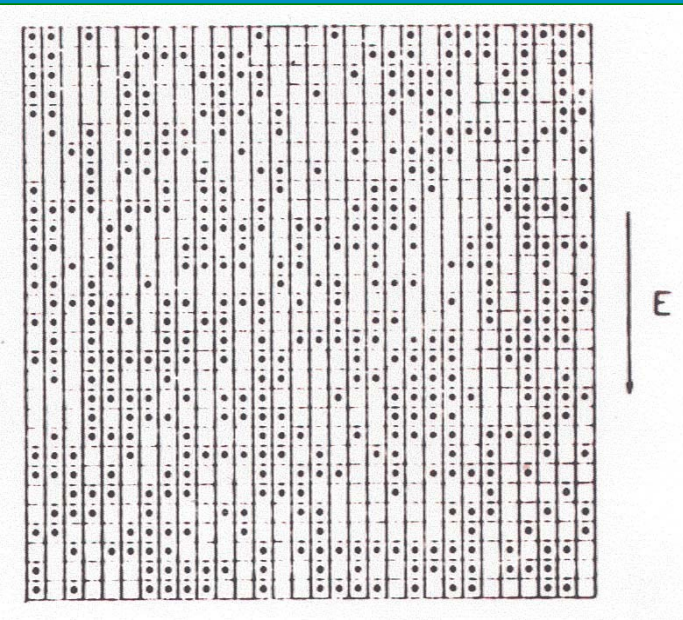


$$D_x = 0, D_y = 1, \quad p = q = 0.005$$

The wavelength in LHOD model λ grows $\propto t^{0.35}$ **In agreement with the two-field model** (Cuerno et al)

In LCOD: $\lambda \propto t^{0.2}$

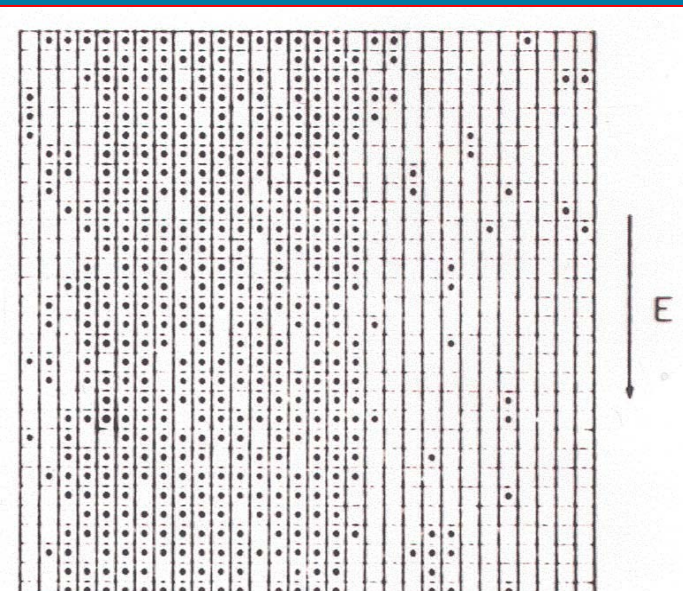
Mapping between Ising Lattice Gas and surface growth



Disordered dimer LG state



„Smooth”, structureless surface



Phase separated state of LG



Surface Patterns

Exploiting analogies with LG

Handy tool to study surfaces, Langevin eqs.

Summary

- KPZ, LHOD, LCOD models created exhibiting MBE, MH scaling in 2d
- Precise numerical results for EW, KPZ, KS scaling exponents, functions
- Understanding of surface growth phenomena via driven lattice gases
- Efficient method to explore scaling and pattern formation → GPUs
- For pattern formation : competing reactions : *KPZ + MBE*
- Wavelength growth scaling via PSD analysis
- UNIVERSALITY DUE TO: $\xi \rightarrow \infty$, CURRENTS, NONEQUILIBRIUM
- See: **Phys. Rev. E** **79** 021125 (2009), **81** 031112 (2010), **81** 051114 (2010)
arXiv:1109.2717 (Applied Surface Science in press)
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